

**Preliminary Amendment**

Applicant: Michael Kund et al.

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Docket No.: I433.210.101/13.848

Title: **MEMORY CELL AND METHOD FOR FABRICATING A MEMORY DEVICE (As Amended)**

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**IN THE ABSTRACT**

Please replace the Abstract with the following rewritten paragraph:

**Abstract**

**MEMORY CELL AND METHOD FOR FABRICATING A MEMORY DEVICE**  
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**Abstract**

When fabricating a memory cell (11) with an organic storage layer (10) which stores a digital information item, processing of polycrystalline and monocrystalline semiconductor structures in which high temperatures are employed is concluded prior to application of the organic storage layer (10).

(Fig. 2)